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Poster Presentation

## [AMDp1]Oxide TFTs

Thu. Nov 28, 2019 10:40 AM - 1:10 PM Main Hall (1F)

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10:40 AM - 1:10 PM

## [AMDp1-5]Transfer Characteristics of $\text{H}_2\text{O}_2$ -Doped $\text{ZrInZnO}$ Thin Film Transistors

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Keywords:TFTs, Solution-process,  $\text{ZrInZnO}$ , Hydrogen peroxide, Positive bias stress

Solution-processed zirconium-indium-zinc-oxide thin-film transistors (ZIZO TFTs) were fabricated with and without hydrogen peroxide ( $\text{H}_2\text{O}_2$ ). With an incorporation of  $\text{H}_2\text{O}_2$  into the channel layer, threshold voltage shift under positive bias stress were improved. We realized the reduced trap density of ZIZO TFTs with 2 M  $\text{H}_2\text{O}_2$  incorporation.